

Amended claims:

A1

2. (Once Amended) A method of increasing the holding voltage of a LVTSCR structure, comprising forming at least one additional p-region and n-region inside a p-well of the structure to define a p-n junction that is forward biased during normal operation.

3. (Once Amended) A method of increasing the holding voltage of a LVTSCR-like structure having an anode and a cathode, comprising providing an alternative current path from anode to cathode through a p-well of the structure, other than purely the current path from anode to cathode through the p-material of the p-well.

A2

5. (Once Amended) A method of claim 4, wherein the lower resistance current path takes the form of at least one p-n junction that is forward biased under normal operating conditions, formed in the p-well.
